

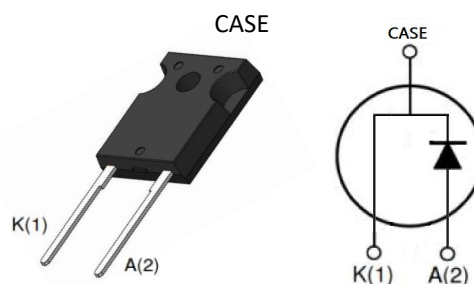
Features

- Ease of Paralleling
- Zero reverse recovery current
- Zero forward recovery voltage
- Temperature independent switching behaviour
- High temperature operation
- High frequency operation

Key Characteristics		
V_{RRM}	1200	V
$I_F, T_c \leq 155^\circ\text{C}$	15	A
Q_c	84	nC

Benefits

- Unipolar rectifier
- Substantially reduced switching losses
- No thermal run-away with parallel devices
- Reduced heat sink requirements



Applications

- Switch Mode Power Supplies (SMPS)
- Boost diodes in PFC or DC/DC stages
- Motor drives
- Solar application, UPS
- Power Switching Circuits

Part No.	Package Type	Marking
ASD15120C	TO-247-2	ASD15120C

Maximum Ratings

Parameter	Symbol	Test Condition	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}		1200	V
Surge Peak Reverse Voltage	V_{RSM}		1200	V
DC Blocking Voltage	V_{DC}		1200	V
Continuous Forward Current	I_F	$T_C=25^{\circ}\text{C}$	55	A
		$T_C=125^{\circ}\text{C}$	30	
		$T_C=155^{\circ}\text{C}$	15	
Repetitive Peak Forward Surge Current	I_{FRM}	$T_C=25^{\circ}\text{C}$, $t_p=10\text{ms}$, Half Sine Wave, $D=0.3$	75	A
Non-repetitive Peak Forward Surge Current	I_{FSM}	$T_C=25^{\circ}\text{C}$, $t_p=10\text{ms}$, Half Sine Wave	204	A
Power Dissipation	P_{TOT}	$T_C=25^{\circ}\text{C}$	263	W
		$T_C=110^{\circ}\text{C}$	114	W
Operating Junction	T_J		-55°C to 175°C	$^{\circ}\text{C}$
Storage Temperature	T_{stg}		-55°C to 175°C	$^{\circ}\text{C}$
Mounting Torque		M3 Screw	1	Nm
		6-32 Screw	8.8	lbf-in

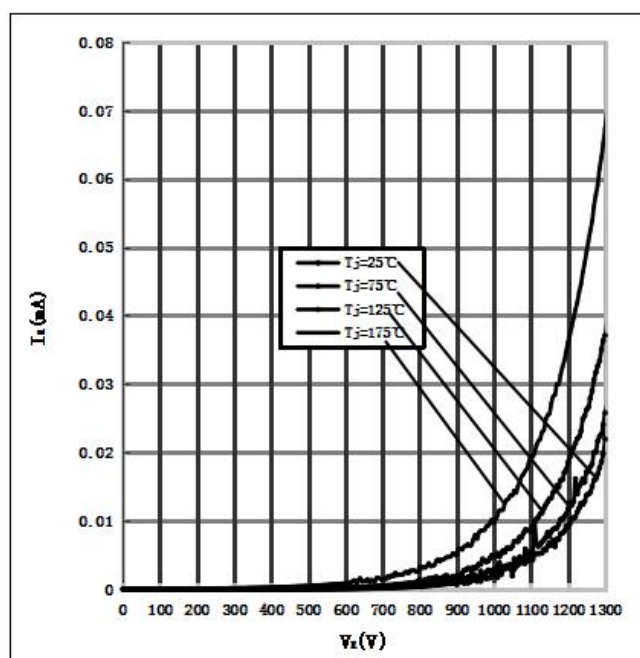
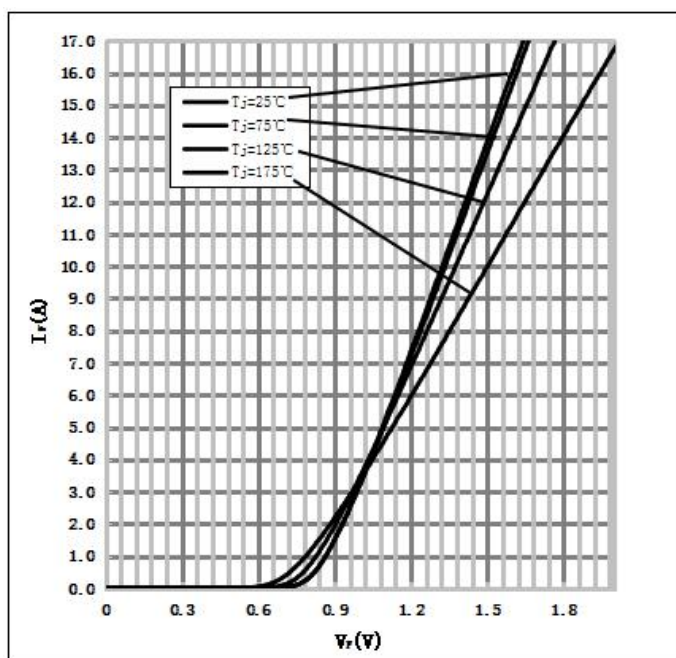
Thermal Characteristics

Parameter	Symbol	Test Condition	Value	Unit
			Typ.	
Thermal resistance from junction to case	R_{thJC}		0.57	$^{\circ}\text{C}/\text{W}$

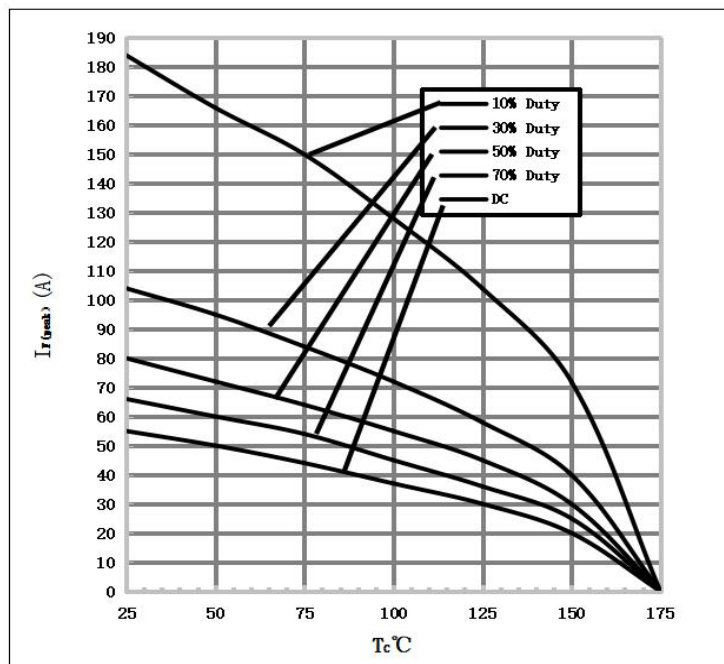


Electrical Characteristics

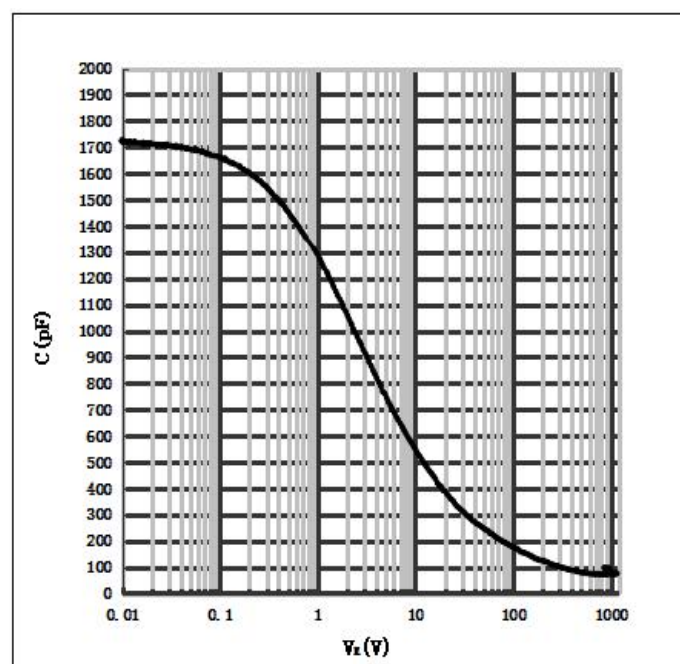
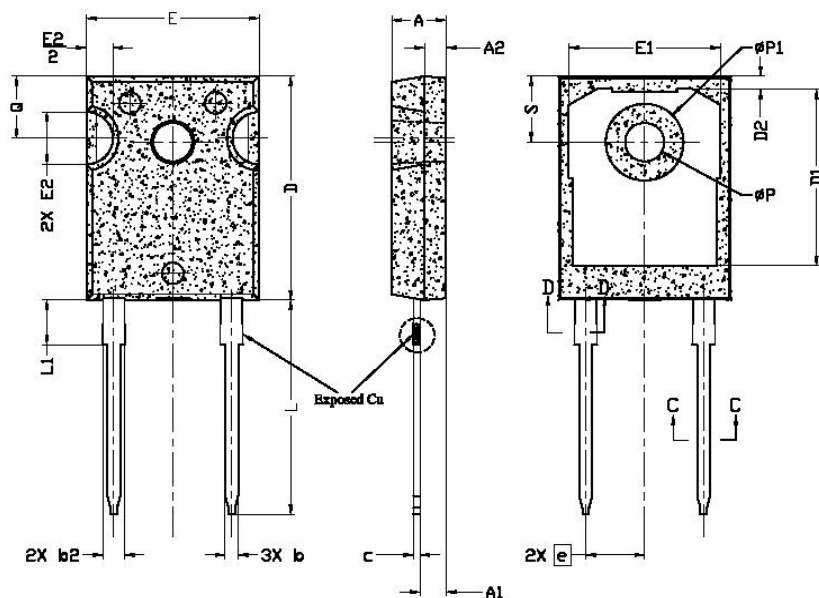
Parameter	Symbol	Test Conditions	Numerical		Unit
			Typ.	Max.	
Forward Voltage	V_F	$I_F=15A, T_J=25^{\circ}C$	1.4	1.7	V
		$I_F=15A, T_J=175^{\circ}C$	2	2.5	
Reverse Current	I_R	$V_R=1200V, T_J=25^{\circ}C$	10	50	μA
		$V_R=1200V, T_J=175^{\circ}C$	20	100	
Total Capacitive Charge	Q_C	$V_R=800V, T_J=150^{\circ}C$ $Q_C = \int_0^{V_R} C(V) dV$	84	-	nC
Total Capacitance	C	$V_R=0V, T_J=25^{\circ}C, f=1MHz$	1370	1420	pF
		$V_R=400V, T_J=25^{\circ}C, f=1MHz$	73	78	
		$V_R=800V, T_J=25^{\circ}C, f=1MHz$	61	63	

Performance Graphs1) Forward IV characteristics as a function of T_J :2) Reverse IV characteristics as a function of T_J :

3) Current Derating



4) Capacitance vs. reverse voltage :

Package TO-247-2

SYMBOL	DIMENSIONS			NOTES
	MIN.	NOM.	MAX.	
A	4,83	5,02	5,21	
A1	2,29	2,41	2,55	
A2	1,50	2,00	2,49	
b	1,12	1,20	1,33	
b1	1,12	1,20	1,28	
b2	1,91	2,00	2,39	6
b3	1,91	2,00	2,34	
c	0,55	0,60	0,69	6
c1	0,55	0,60	0,65	
D	20,80	20,95	21,10	4
D1	16,25	16,55	17,65	5
D2	0,51	1,19	1,35	
E	15,75	15,94	16,13	4
E1	13,46	14,02	14,16	5
E2	4,32	4,91	5,49	3
e	5,44BSC			
L	19,81	20,07	20,32	
L1	4,10	4,19	4,40	6
ØP	3,56	3,61	3,65	7
ØP1	7,19REF.			
Q	5,39	5,79	6,20	
S	6,04	6,17	6,30	

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